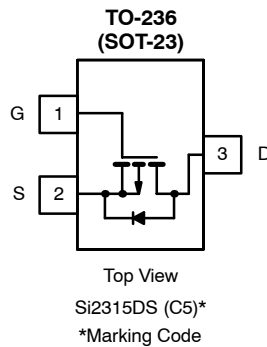




P-Channel 1.25-W, 1.8-V (G-S) MOSFET

TrenchFET[®]
Power MOSFETs
1.8-V Rated

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-12	0.055 @ $V_{GS} = -4.5$ V	± 3.5
	0.075 @ $V_{GS} = -2.5$ V	± 3
	0.118 @ $V_{GS} = -1.8$ V	± 2



Ordering Information: Si2315DS-T1

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	-12	V
Gate-Source Voltage		V_{GS}	± 8	
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^{a, b}	$T_A = 25^\circ\text{C}$	I_D	± 3.5	A
	$T_A = 70^\circ\text{C}$		± 2.8	
Pulsed Drain Current		I_{DM}	± 12	
Continuous Source Current (Diode Conduction) ^{a, b}		I_S	-1.6	
Maximum Power Dissipation ^{a, b}	$T_A = 25^\circ\text{C}$	P_D	1.25	W
	$T_A = 70^\circ\text{C}$		0.8	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ sec	R_{thJA}		100	$^\circ\text{C/W}$
	Steady State		130		

Notes

- a. Surface Mounted on FR4 Board.
- b. $t \leq 5$ sec.

For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>



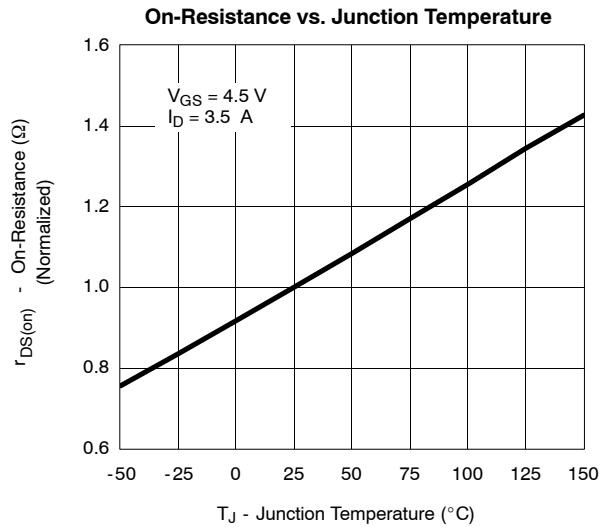
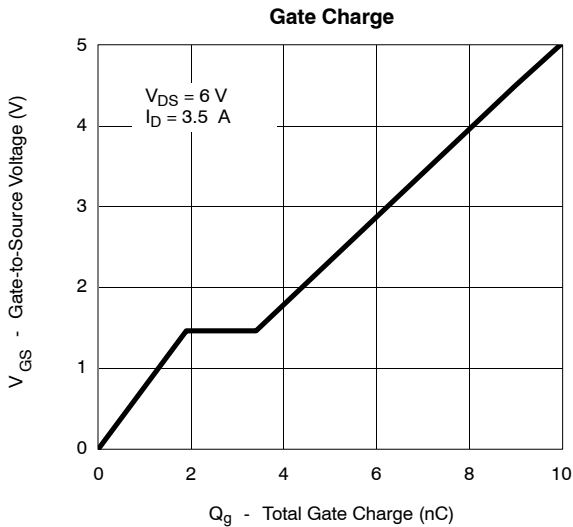
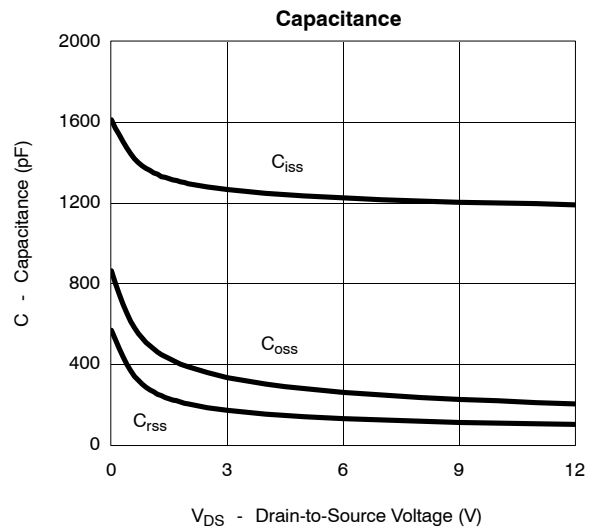
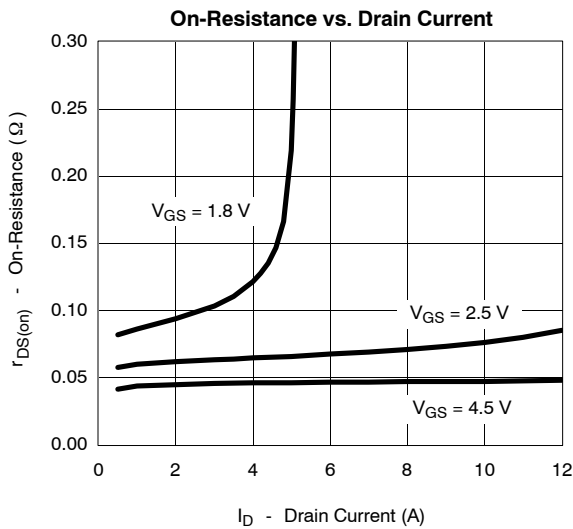
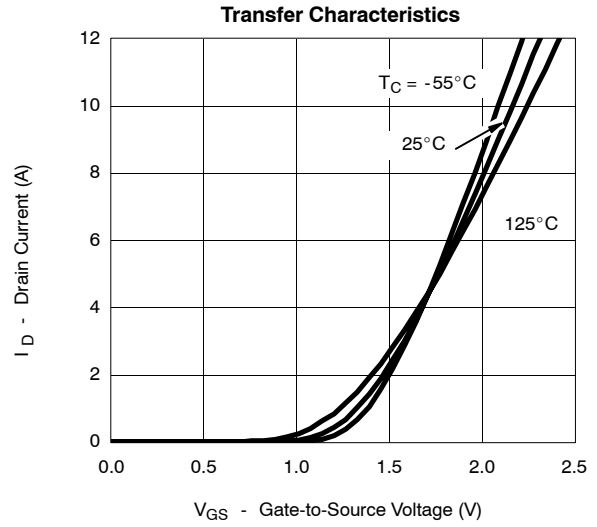
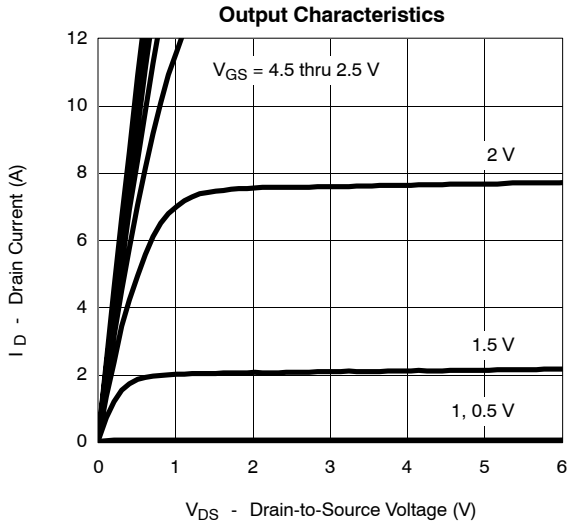
SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -10\ \mu\text{A}$	-12			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.45			
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -12\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -12\text{ V}, V_{GS} = 0\text{ V}, T_J = 55^\circ\text{C}$			-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$	-6			A
		$V_{DS} \leq -5\text{ V}, V_{GS} = -2.5\text{ V}$	-3			
Drain-Source On-Resistance ^a	$r_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -3.5\text{ A}$		0.045	0.055	Ω
		$V_{GS} = -2.5\text{ V}, I_D = -3\text{ A}$		0.063	0.075	
		$V_{GS} = -1.8\text{ V}, I_D = -2\text{ A}$		0.093	0.118	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -5\text{ V}, I_D = -3.5\text{ A}$		7		S
Diode Forward Voltage	V_{SD}	$I_S = -1.6\text{ A}, V_{GS} = 0\text{ V}$			-1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -6\text{ V}, V_{GS} = -4.5\text{ V}$ $I_D \cong -3.5\text{ A}$		9	15	nC
Gate-Source Charge	Q_{gs}			1.9		
Gate-Drain Charge	Q_{gd}			1.5		
Input Capacitance	C_{iss}	$V_{DS} = -6\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$		1225		pF
Output Capacitance	C_{oss}			260		
Reverse Transfer Capacitance	C_{rss}			130		
Switching^b						
Turn-On Time	$t_{d(on)}$	$V_{DD} = -6\text{ V}, R_L = 6\ \Omega$ $I_D \cong -1.0\text{ A}, V_{GEN} = -4.5\text{ V}$ $R_G = 6\ \Omega$		13.0	20	ns
	t_r			15	25	
Turn-Off Time	$t_{d(off)}$			50	70	
	t_f			19	35	

Notes

- For DESIGN AID ONLY, not subject to production testing.
- Pulse test: $PW \leq 300\ \mu\text{s}$ duty cycle $\leq 2\%$.
- Switching time is essentially independent of operating temperature.



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



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